

Donors / acceptors:

Equilibrium :

typically all ionized, wide range of T

(density not too big)

Donors: pull μ toward CB edge.

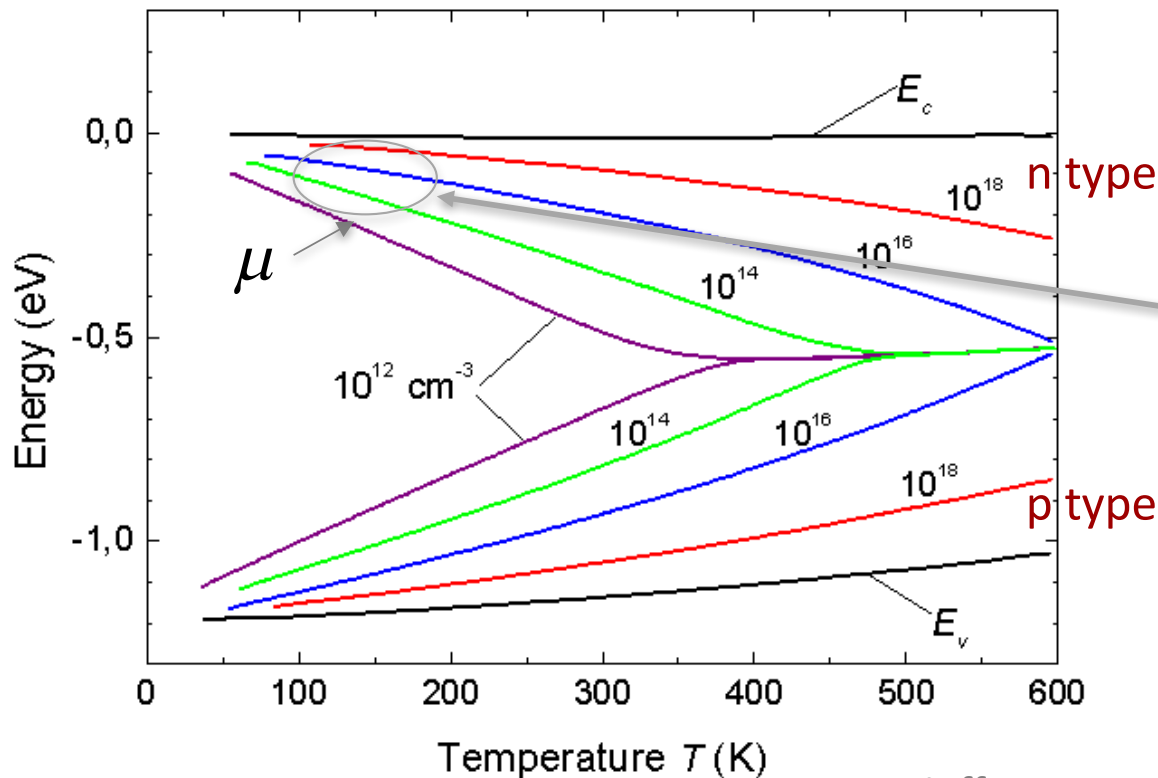
prob. of ionized donor

$$n - p = N_d \left[1 - \frac{1}{1 + \frac{1}{2} e^{(\varepsilon_d - \mu)/kT}} \right]$$

$$n \approx N_c(T) e^{-(\varepsilon_c - \mu)/kT}$$

$$p \approx P_v(T) e^{-(\mu - \varepsilon_v)/kT}$$

Solve for μ .



Example suppose:

$$\varepsilon_c - \varepsilon_d = k_B \times (\text{room temperature})$$

$$N_c = 10^{19} [T/RT]^{3/2}$$

$$N_D = 10^{15} \leftarrow (\text{in cm}^{-3})$$

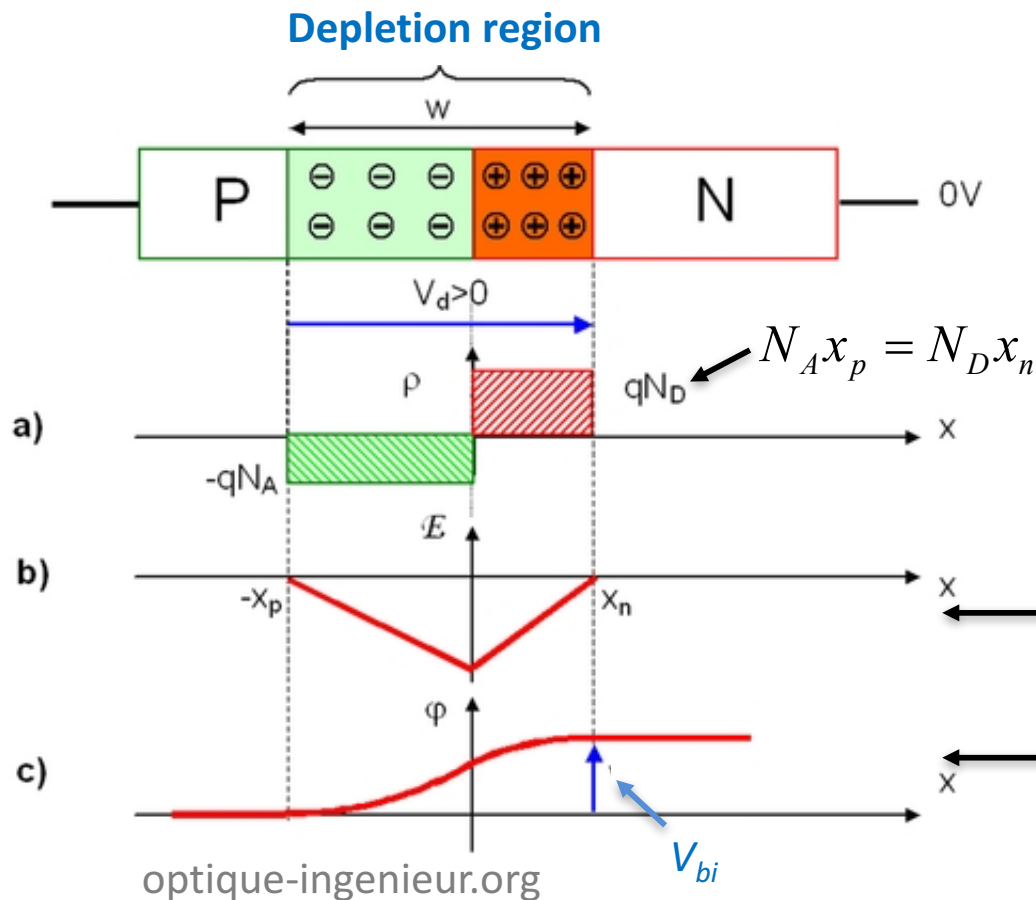
$$N_c = 1.9 \times 10^{18}$$

Then if $T = RT/3 \approx 100$ K,

$$\text{Solve} \rightarrow n = 0.98 \times N_D = 9.8 \times 10^{14}$$

$$\varepsilon_c - \mu = 7.58 \times (k_B T) \approx 0.063 \text{ eV}$$

Semiconductor p-n junctions:

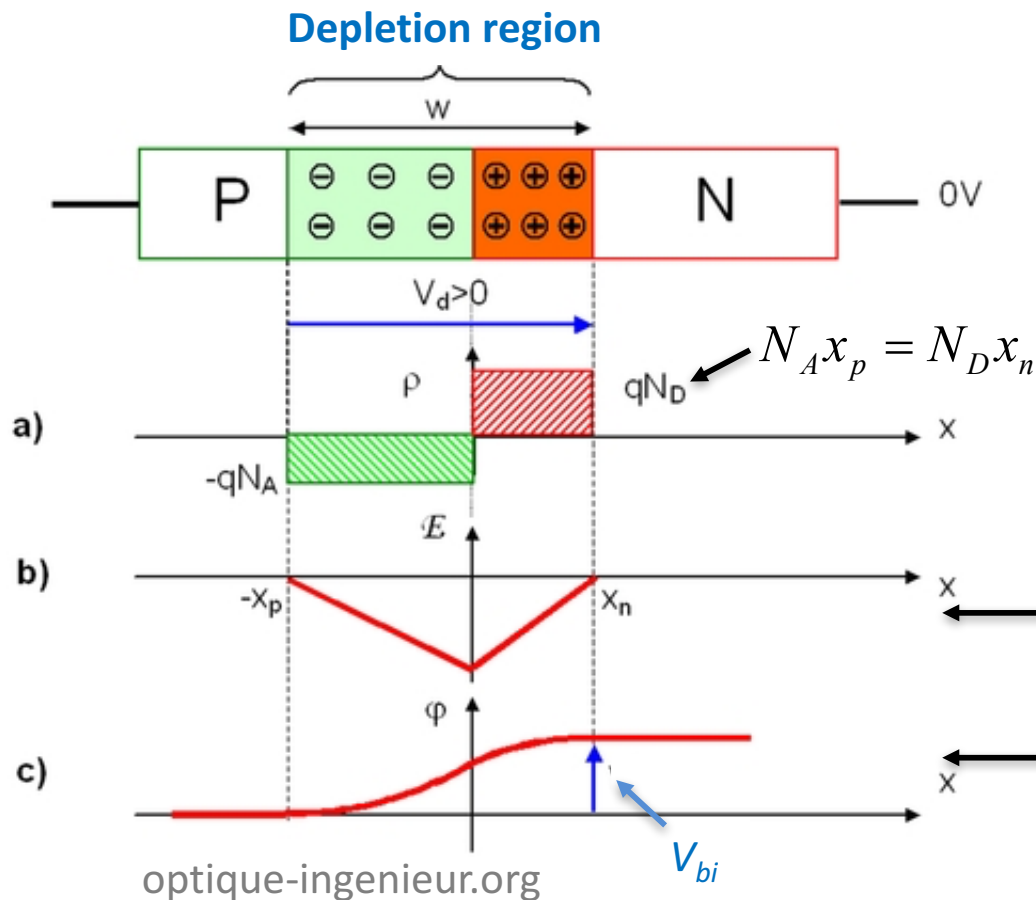


- Depletion region: high resistivity
- Width W determined by donor/acceptor density
- “Built in voltage” V_{bi} set by chemical potentials in p & n regions (eV_{bi} close to ε_g).

$$E_{p,n} = E_o \pm 4\pi N_{A,D} ex / \kappa$$

$$\Delta V_p = \frac{2\pi N_A ex_p^2}{\kappa} \quad \Delta V_n = \frac{2\pi N_D ex_n^2}{\kappa}$$

Semiconductor p-n junctions:



- Depletion region: high resistivity
- Width W determined by donor/acceptor density
- “Built in voltage” V_{bi} set by chemical potentials in p & n regions (eV_{bi} close to ε_g).

$$E_{p,n} = E_o \pm 4\pi N_{A,D} ex / \kappa$$

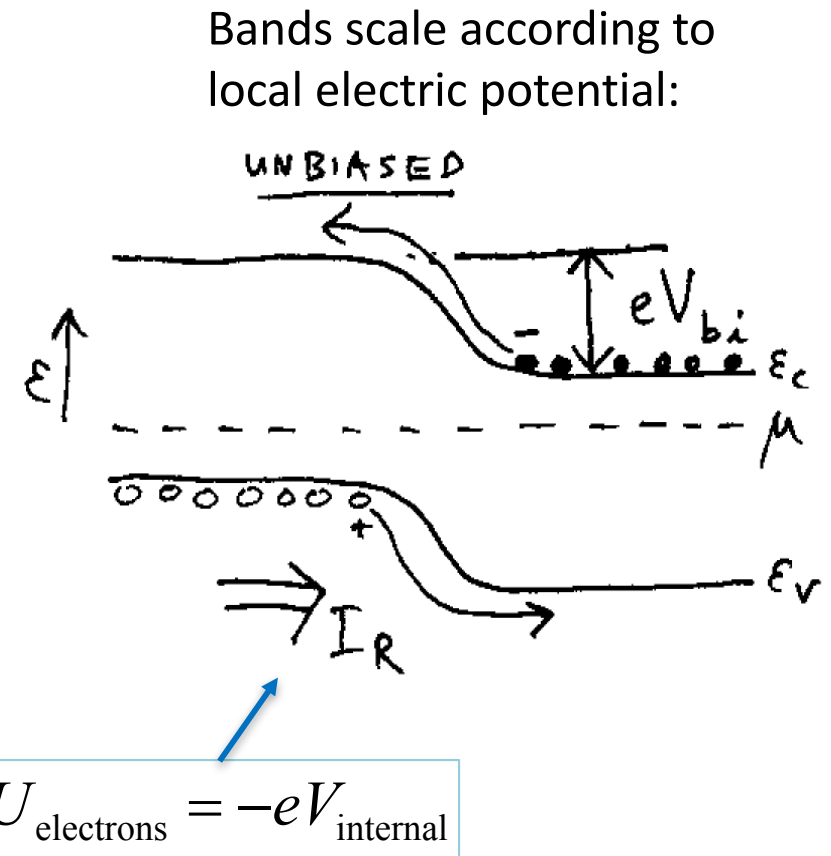
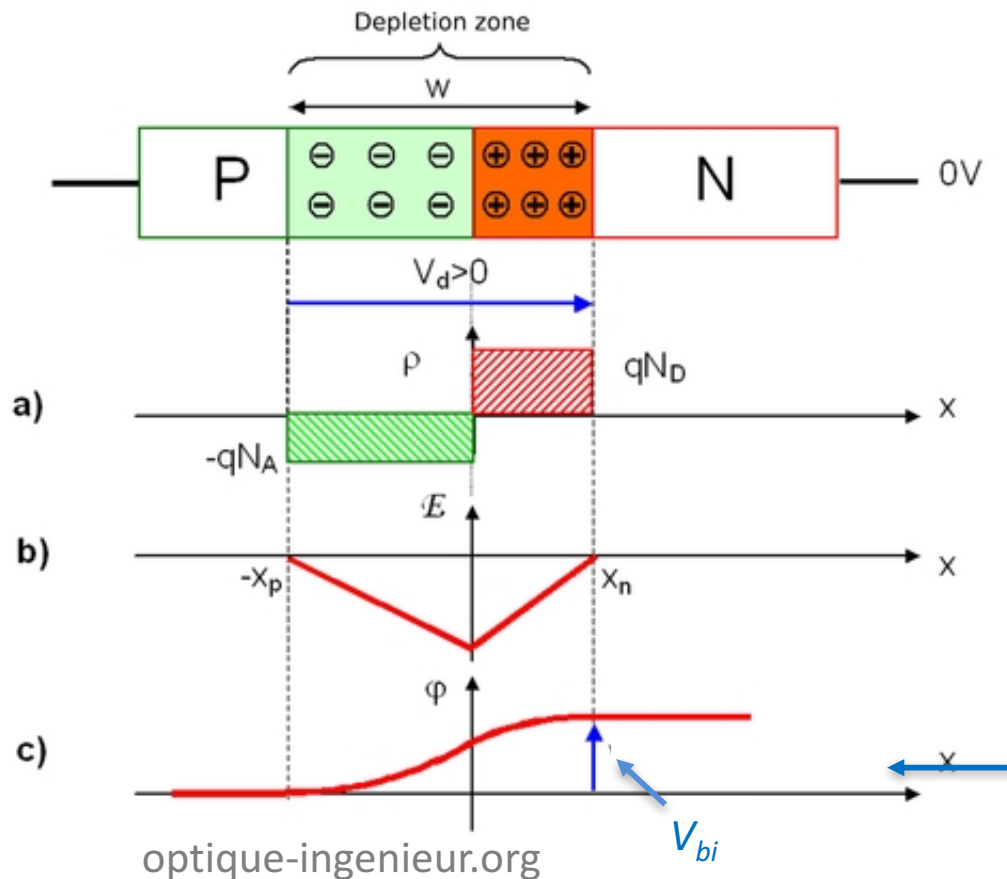
$$\Delta V_p = \frac{2\pi N_A ex_p^2}{\kappa} \quad \Delta V_n = \frac{2\pi N_D ex_n^2}{\kappa}$$



Typical, $W \approx 1 \mu\text{m}$
 (Si, $N_A = N_D = 10^{15} \text{ cm}^{-3}$)

$$x_n = \sqrt{\frac{\kappa V_{bi} N_A}{2\pi N_D e (N_A + N_D)}}$$

Semiconductor p-n junctions:



Note, chemical potential is what is measured externally (e.g. with ideal voltmeter)

Also note, we assumed here V varies slowly. (OK if donor densities not too large)